

forming at least one semiconductor layer on said porous layer; and

separating said semiconductor layer from said substrate by forming a mechanical rupture in said porous layer.

98. A method for separating a semiconductor layer from a substrate according to claim <sup>97</sup>~~1~~<sub>1</sub>, wherein said substrate is a Si substrate.

99. A method for separating a semiconductor layer from a substrate according to claim <sup>97</sup>~~1~~<sub>1</sub>, wherein said porous layer is a Si porous layer.

100. A method for separating a semiconductor layer from a substrate according to claim <sup>97</sup>~~1~~<sub>1</sub>, wherein the method further comprises a step of oxidizing said porous layer after forming said porous layer.

101. A method for separating a semiconductor layer from a substrate according to claim <sup>100</sup>~~1~~<sub>1</sub>, wherein said porous layer is oxidized at a temperature of 400°.

102. A method for separating a semiconductor layer from a substrate comprising:

forming a porous layer on a surface of a substrate;

oxidizing said porous layer;